

Super J MOS® S2/S2FD Series

# Super-Junction Technology Supports Enhanced Efficiency and Compactness

Optimizing the concentration of the impurity layer in a super-junction structure greatly improved the trade-off between device withstand voltage and on-resistance compared with conventional products (Super J MOS<sup>®</sup> S1 Series). Keeping the trade-off characteristics between turn-off loss and turn-off dv/dt at the same level as conventional products enables both low-loss and low-noise characteristics, and supports enhanced efficiency and compactness of a power supply.

- Achieve highly efficient power supply: About 30% reduction in gate charge ( $Q_G$ ) and output charge/discharge loss ( $E_{oss}$ ) compared with conventional products
- Enable package downsizing: About 25% reduction in on-resistance (R<sub>DS(on)</sub>·A) compared with conventional products
- · Suppress surge voltage during turn-off
- S2FD Series: About 50% reduction in reverse recovery time (*t*<sub>rr</sub>) of the built-in diode compared with the standard type (S2 Series)
- Adds the DFN 8×8 package to the lineup Super J MOS<sup>®</sup> is a registered trademark of Fuji Electric.



Package: DFN8×8, TO-220F TO-220, TO-3P, TO-247

Application examples: Server, communication equipment, LED light, UPS, power conditioning sub-system, general-purpose power supply, quick charger for EV, etc.

# 1. About 30% reduction in gate charge ( $Q_G$ ) and output charge/discharge loss ( $E_{oss}$ ) compared with conventional products





# 3. S2FD: About 50% reduction in $t_{rr}$ (compared with S2)

#### Comparison of reverse recovery time $(t_{rr})$



Conditions:  $V_{\text{DD}}$ =400V,  $I_{\text{DR}}$ =39.4A,  $-di_{\text{DR}}/dt$ =100A/us,  $T_{\text{ch}}$ =25°C

## 400

Conditions: Booster circuit,  $V_{\rm DD}$ =400V,  $I_{\rm D}$ =39.4A,  $V_{\rm GS}$ =10/0V,  $T_{\rm ch}$ =25°C

# 4. Addition of new SMD DFN 8×8\*<sup>1</sup> package

- · Comes with a sub-source terminal to reduce the effect of common source inductance on the gate drive voltage
- · Uses a leadless package to reduce ringing via fewer inductors

Significantly reduces turn-off loss and turn-on loss compared to the TO-220 package

Super J MOS<sup>®</sup> S2 Series

#### 300 TO-220 Package Back side 250 200 ß ß 150 DFN8x8 PWM щ щ 100 50 0 0 5 10 15 20 External RG off [ohm]



FMW60N027S2FD

### Super J MOS<sup>®</sup> S2FD Series

V <sub>DSS</sub>	R <sub>DS(on)</sub> (mΩ)	Product Type & Package				V <sub>DSS</sub>	R <sub>DS(on)</sub>	Product Type & Package			
(V)		TO-220	TO-220F(SLS)	TO-3P(Q)	TO-247(Type:B)	(V)	(mΩ) ໌	DFN8x8	TO-220	TO-220F(SLS)	TO-247(Type:B)
	380	FMP60N380S2	FMV60N380S2				191	FML60N191S2FD			
600	280	FMP60N280S2	FMV60N280S2	FMH60N280S2			170		FMP60N170S2FD	FMV60N170S2FD	FMW60N170S2FD
	190	FMP60N190S2	FMV60N190S2	FMH60N190S2	FMW60N190S2		150	FML60N150S2FD			
	160	FMP60N160S2	FMV60N160S2		FMW60N160S2		133		FMP60N133S2FD	FMV60N133S2FD	FMW60N133S2FD
	125	FMP60N125S2	FMV60N125S2		FMW60N125S2		118	FML60N118S2FD			
	99	FMP60N099S2	FMV60N099S2		FMW60N099S2		105		FMP60N105S2FD	FMV60N105S2FD	FMW60N105S2FD
	88	FMP60N088S2	FMV60N088S2		FMW60N088S2	000	104	FML60N104S2FD			
	79	FMP60N079S2	FMV60N079S2		FMW60N079S2	600	94		FMP60N094S2FD	FMV60N094S2FD	FMW60N094S2FD
	70		FMV60N070S2		FMW60N070S2		93	FML60N093S2FD			
	55				FMW60N055S2		84		FMP60N084S2FD	FMV60N084S2FD	FMW60N084S2FD
	40				FMW60N040S2		75			FMV60N075S2FD	FMW60N075S2FD
	25.4				FMW60N025S2		59				FMW60N059S2FD
							43				FMW60N043S2FD

%1 DFN(Dual Flat No-lead)

### ▲ Safety Precautions

\* Before using this product, read the "Instruction Manual" and "Specifications" carefully, and consult with the retailer from which you purchased this product as necessary to use this product correctly \* The product must be handled by a technician with the appropriate skills.

# Euli Electric Co. 1td

#### URL www.fujielectric.com/products/semiconductor/

FUJI Electric Co.	, LLO. Gate City Ohsaki, East Tower, 1-11-2, Osaki, Shinagawa-ku, Tokyo 141-0032, Japan T	el:+81-3-5435-7156	
• Fuji Electric Hong Kong Co., Ltd.	Unit 1601-03 & 05, 16/F., Tower II, Grand Century Place, No. 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong	Tel: +852-2664-8699	
<ul> <li>Fuji Electric Taiwan Co., Ltd.</li> </ul>	10F. No.168, Song Jiang Road, Taipei, Taiwan	Tel: +886-2-2515-1820	
<ul> <li>Fuji Electric Asia Pacific Pte. Ltd.</li> </ul>	151 Lorong Chuan, #03-01/01A, New Tech Park, SINGAPORE 556741	Tel: +65-6533-0014	
<ul> <li>Fuji Electric India Private Ltd.</li> </ul>	119(Part), 120, 120A, Electrical and Electronics Industrial Estate, Perungudi, Chennai - 600096, Tamil Nadu, India	Tel: +91-44-40004200	
<ul> <li>Fuji Electric Corp. of America</li> </ul>	50 Northfield Avenue Edison, NJ 08837, USA	Tel: +1-732-560-9410	
<ul> <li>Fuji Electric Europe GmbH</li> </ul>	Goethering 58, 63067 Offenbach am Main, F.R. GERMANY	Tel: +49-69-6690290	2021-8 FOLS PDF

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# 2. Suppressed surge voltage during turn-off Comparison of surge voltage during turn-off (V<sub>DS</sub> surge)

650

S2: FMW60N070S2 (600V/70mΩ max.) S1: FMW47N60S1 (600V/70mΩ max.)



Comparison between S2 and S1 Series